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N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (Ω) TYP. I_D (A) d		Q _g (TYP.)		
40	0.0011 at V _{GS} = 10 V	220	155		
40	0.0018 at V _{GS} = 4.5 V	180	155		

FEATURES

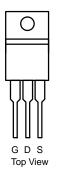
- DT-Trench Power MOSFET
- Maximum 175 °C junction temperature

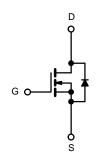


- Operable with logic-level gate drive
- 100 % R_g and UIS tested



TO-220AB





N-Channel MOSFET

APPLICATIONS

- Power supply
- Secondary synchronous rectification
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	40	V			
Gate-Source Voltage	V _{GS}	± 20] v			
Continuous Drain Current (T, I = 150 °C)	T _C = 25 °C		220 ^d			
Continuous Drain Current (1) = 150 °C)	T _C = 70 °C	I _D	190 ^d	Α		
Pulsed Drain Current (t = 100 μs)	I _{DM}	1320				
Avalanche Current	L = 0.1 mH	I _{AS}	200			
Single Avalanche Energy ^a	L = 0.1 mn	E _{AS}	1380	mJ		
Maximum Daway Dissipation 8	T _C = 25 °C	В	450 ^b	W		
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	195 ^b	VV		
Operating Junction and Storage Temperature Ra	inge	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	35	°C/W			
Junction-to-Case (Drain)	R_{thJC}	0.4	C/W			

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).
- d. Package limited.



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40	-	-	- 3.0 V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0	-	3.0		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		V _{DS} = 40 V, V _{GS} = 0 V	-	-	1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150		
		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	220	-	-	Α	
Drain-Source On-State Resistance a	D	V _{GS} = 10 V, I _D = 30 A	-	0.0011	0.0015	Ω	
Drain-Source On-State Resistance 4	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 20 \text{ A}$	-	0.0018	0.0026		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 30 \text{ A}$	-	179	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	18210	-	pF	
Output Capacitance	Coss	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	-	2000	-		
Reverse Transfer Capacitance	C _{rss}		-	350	-		
Total Gate Charge ^c	Qg		-	155	230	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	30	-		
Gate-Drain Charge ^c	Q_{gd}		-	11	-		
Gate Resistance	R _g	f = 1 MHz		1.7		Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	17	30		
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, R_L = 5 \Omega$	-	22	41		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10$ A, $V_{GEN} = 10$ V, $R_g = 1$ Ω	-	66	101	ns	
Fall Time ^c	t _f		-	15	31		
Drain-Source Body Diode Ratings ar	nd Characteris	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 μs)	I _{SM}		-	-	1320	Α	
Forward Voltage ^a	V_{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V	
Reverse Recovery Time	t _{rr}		-	130	205	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 41 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	5	10	Α	
Reverse Recovery Charge	Q _{rr}		-	0.340	0.510	μC	

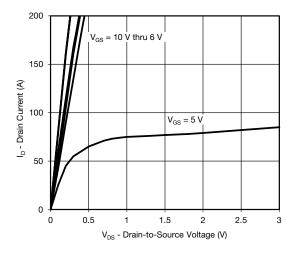
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

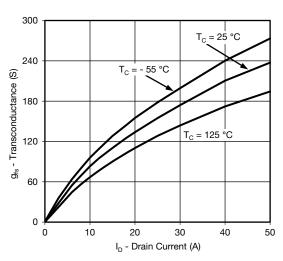
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



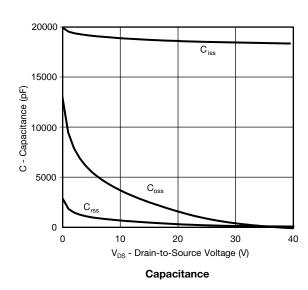
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

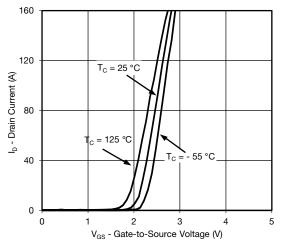


Output Characteristics

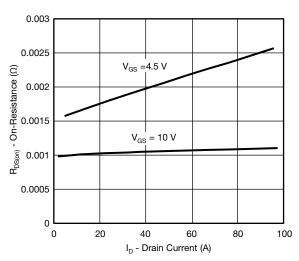


Transconductance

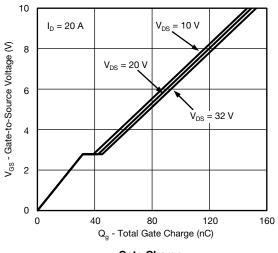




Transfer Characteristics



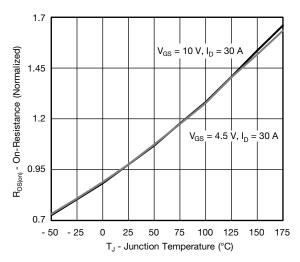
On-Resistance vs. Drain Current



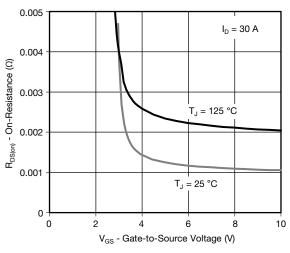
Gate Charge



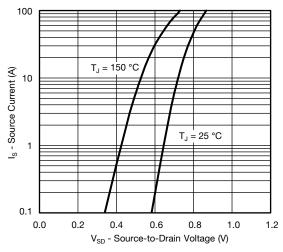
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



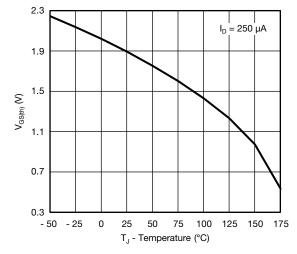
On-Resistance vs. Junction Temperature



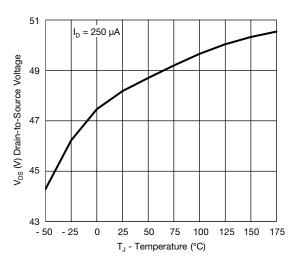
On-Resistance vs. Gate-to-Source Voltage



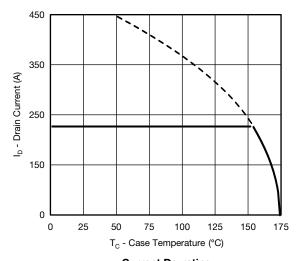
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

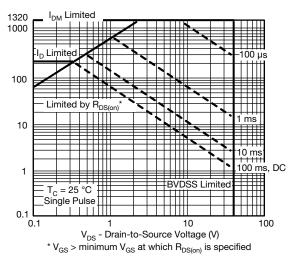


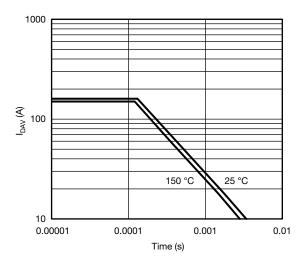
Current De-rating



I_D - Drain Current (A)

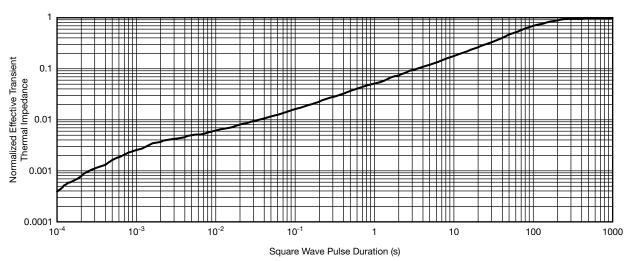
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)





Safe Operating Area

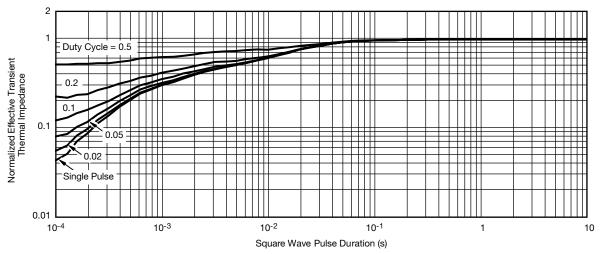
Single Pulse Avalanche Current Capability vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

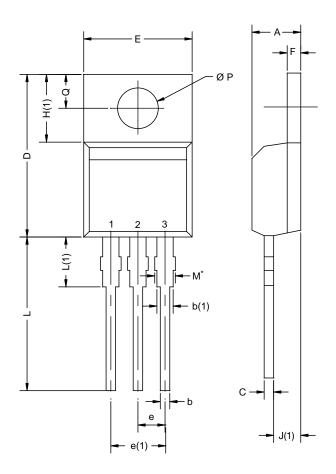
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



TO-220AB



	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
E	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471					

Notes

 $^{^{*}}$ M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM





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